



## 7N65K-MTQ

Power MOSFET

### 7A, 650V N-CHANNEL POWER MOSFET

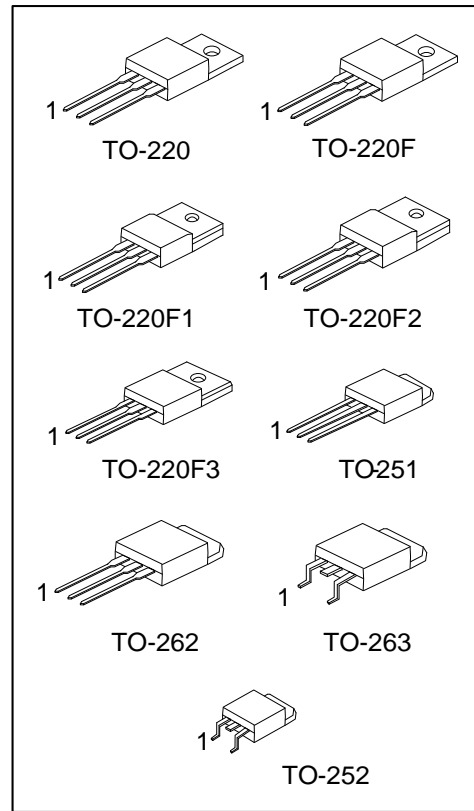
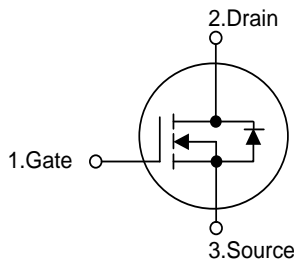
#### DESCRIPTION

The UTC 7N65K-MTQ is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

#### FEATURES

- \*  $R_{DS(ON)} \leq 1.6 \Omega @ V_{GS}=10V, I_D=3.5A$
- \* Fast switching capability
- \* Avalanche energy tested
- \* Improved dv/dt capability, high ruggedness

#### SYMBOL



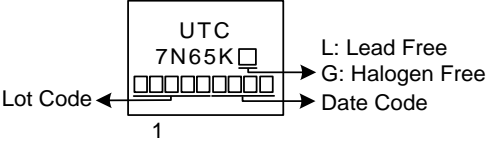
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N65KL-TA3-T	7N65KG-TA3-T	TO-220	G	D	S	Tube
7N65KL-TF3-T	7N65KG-TF3-T	TO-220F	G	D	S	Tube
7N65KL-TF1-T	7N65KG-TF1-T	TO-220F1	G	D	S	Tube
7N65KL-TF2-T	7N65KG-TF2-T	TO-220F2	G	D	S	Tube
7N65KL-TF3T-T	7N65KG-TF3T-T	TO-220F3	G	D	S	Tube
7N65KL-TM3-T	7N65KG-TM3-T	TO-251	G	D	S	Tube
7N65KL-TN3-R	7N65KG-TN3-R	TO-252	G	D	S	Tape Reel
7N65KL-T2Q-T	7N65KG-T2Q-T	TO-262	G	D	S	Tube
7N65KL-TQ2-T	7N65KG-TQ2-T	TO-263	G	D	S	Tube
7N65KL-TQ2-R	7N65KG-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>7N65KG-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220F, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TN3: TO-252, T2Q: TO-262, TQ3: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



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### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V <sub>DSS</sub>	650	V
Gate-Source Voltage		V <sub>GSS</sub>	±30	V
Continuous Drain Current		I <sub>D</sub>	7	A
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	24	A
Avalanche Current (Note 2)		I <sub>AR</sub>	7	A
Avalanche Energy, Repetitive, Limited by T <sub>JMAX</sub>		E <sub>AR</sub>	2	mJ
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	350	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262 TO-263	P <sub>D</sub>	125	W
	TO-220F/TO-220F1 TO-220F2/TO-220F3		38	W
	TO-251/TO-252		55	W
Junction Temperature		T <sub>J</sub>	+150	°C
Operating Temperature		T <sub>OPR</sub>	-55 ~ +150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 14.28mH, I<sub>AS</sub> = 7A, V<sub>DD</sub> = 90V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C

4. I<sub>SD</sub> ≤ 7A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C

### ■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT			
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3/TO-262 TO-263	θ <sub>JA</sub>	62.5	°C/W			
	TO-251/TO-252		110				
	Junction to Case		TO-220/TO-262 TO-263		θ <sub>JC</sub>	1.0	°C/W
			TO-220F/TO-220F1 TO-220F2/TO-220F3			3.29	
TO-251/TO-252		2.27 (Note)					

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

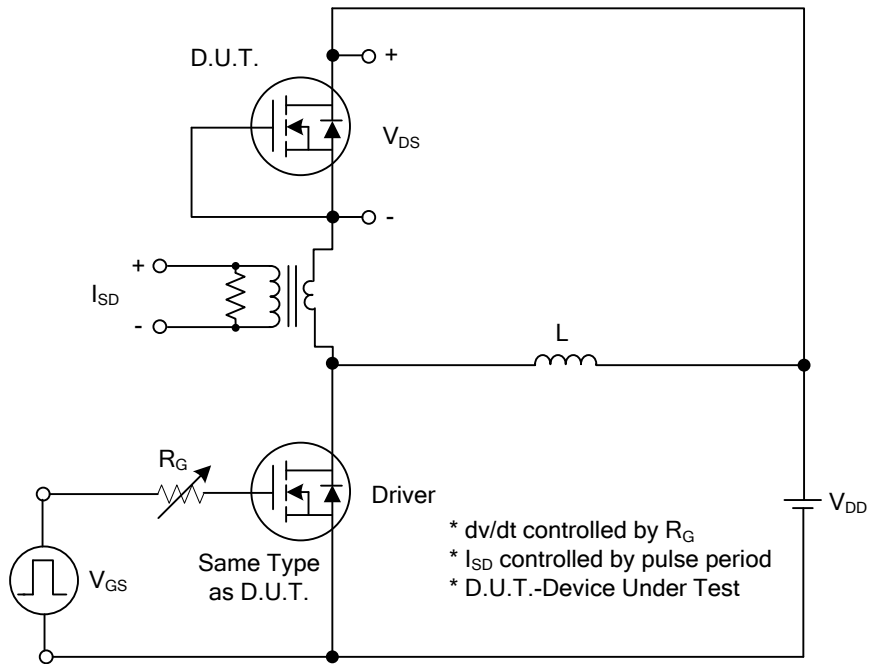
■ **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V$			10	$\mu A$
Gate- Source Leakage Current	Forward	$I_{GSS}$			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\mu A$ , Referenced to $25^\circ\text{C}$		0.53		$V/^\circ\text{C}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.5A$			1.6	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		980		pF
Output Capacitance	$C_{OSS}$			90		pF
Reverse Transfer Capacitance	$C_{RSS}$			5		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge	$Q_G$	$V_{DS} = 200V, I_D = 7.0A, V_{GS} = 10V$ $I_G = 3mA$ (Note 1, 2)		24.1		nC
Gate-Source Charge	$Q_{GS}$			7.2		nC
Gate-Drain Charge	$Q_{GD}$			6		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, I_D = 0.5A, V_{GS} = 10V$ $R_G = 25\Omega$ (Note 1, 2)		50		ns
Turn-On Rise Time	$t_R$			65		ns
Turn-Off Delay Time	$t_{D(OFF)}$			110		ns
Turn-Off Fall Time	$t_F$			55		ns
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				7	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$				28	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 7A$			1.4	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_S = 7A, di/dt = 100A/\mu s$		320		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$				2.4	

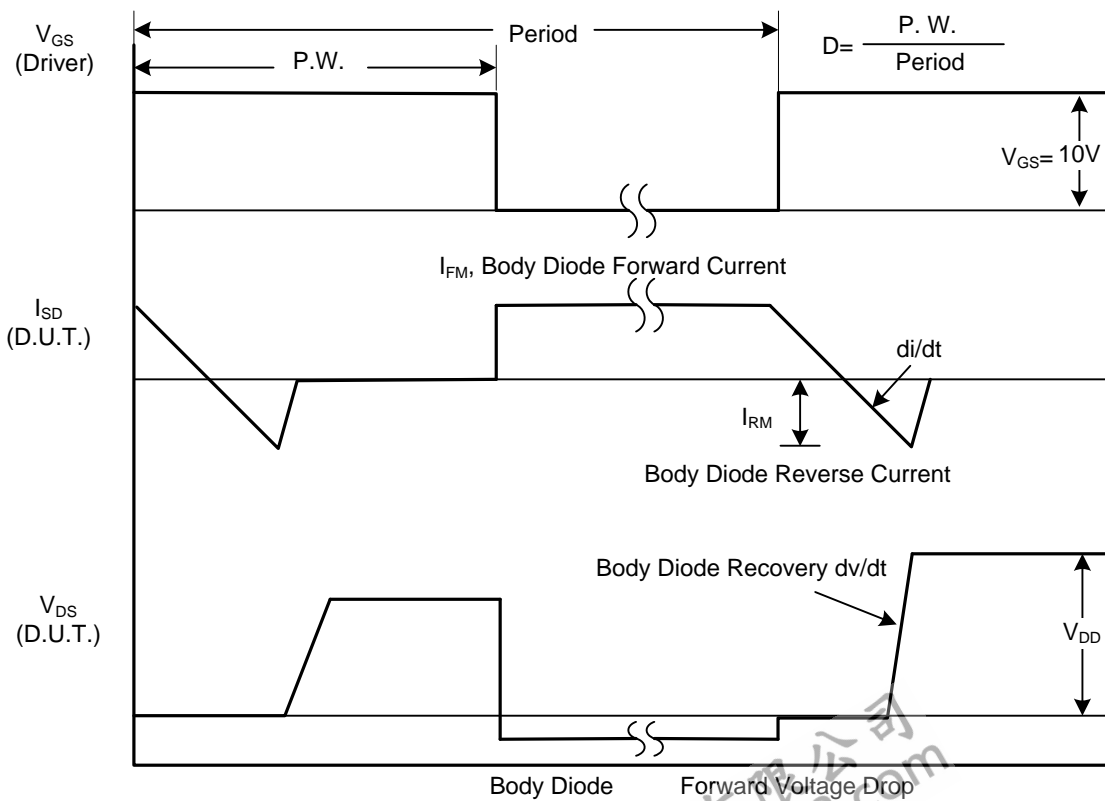
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$

2. Essentially independent of operating temperature

## TEST CIRCUITS AND WAVEFORMS

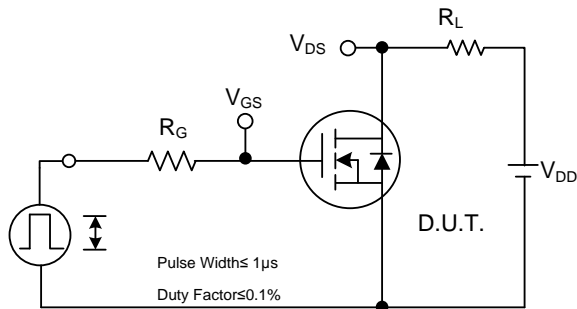


Peak Diode Recovery dv/dt Test Circuit

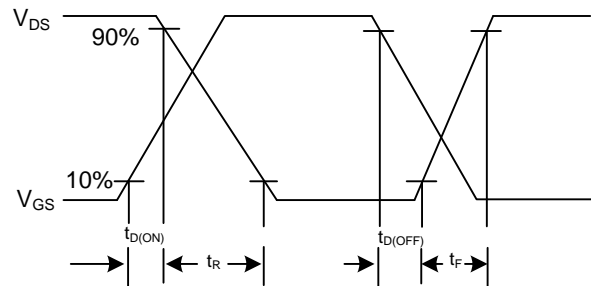


Peak Diode Recovery dv/dt Waveforms

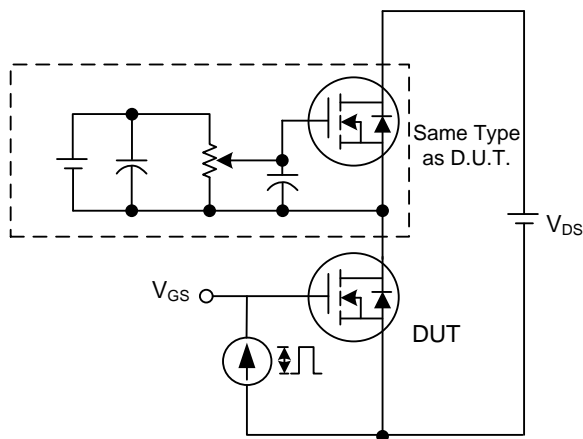
## TEST CIRCUITS AND WAVEFORMS



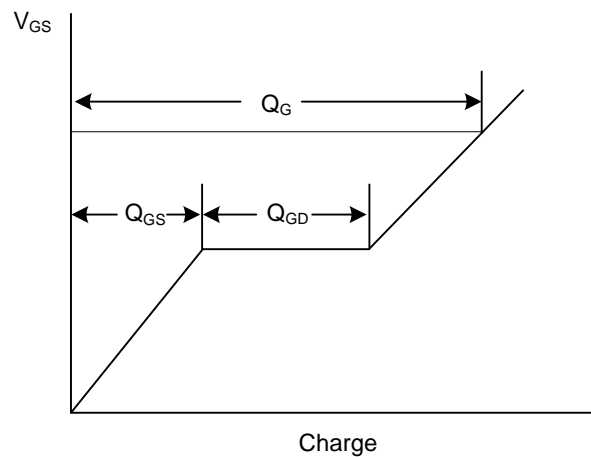
Switching Test Circuit



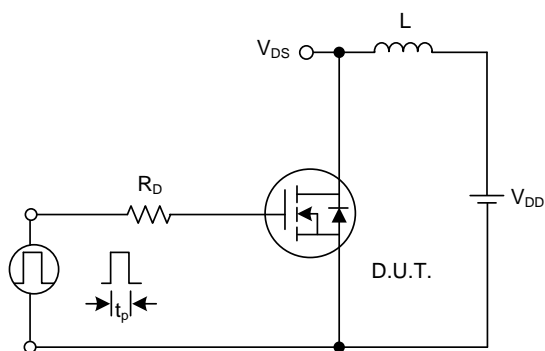
Switching Waveforms



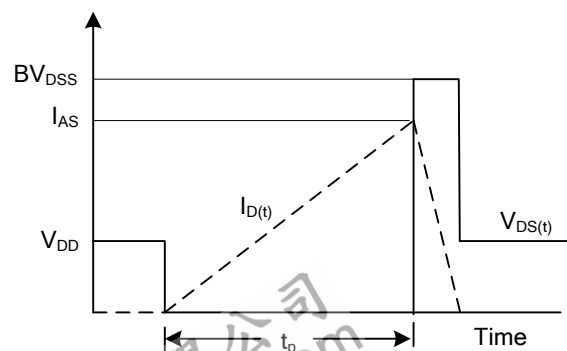
Gate Charge Test Circuit



Gate Charge Waveform

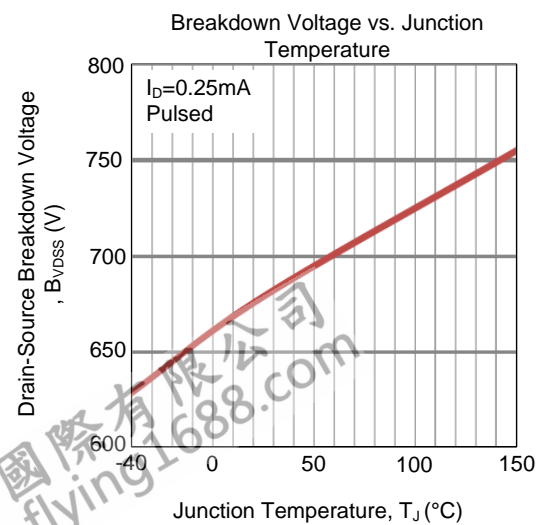
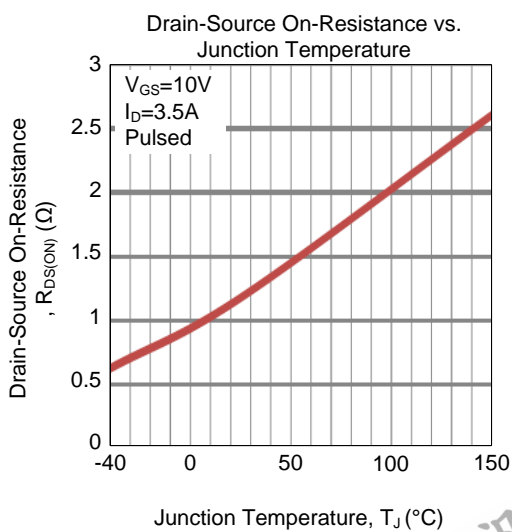
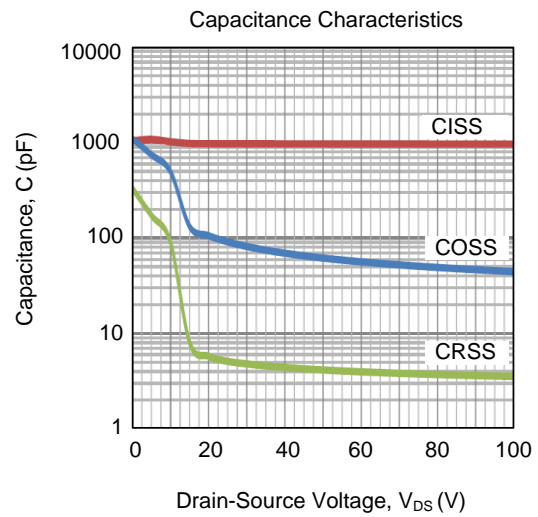
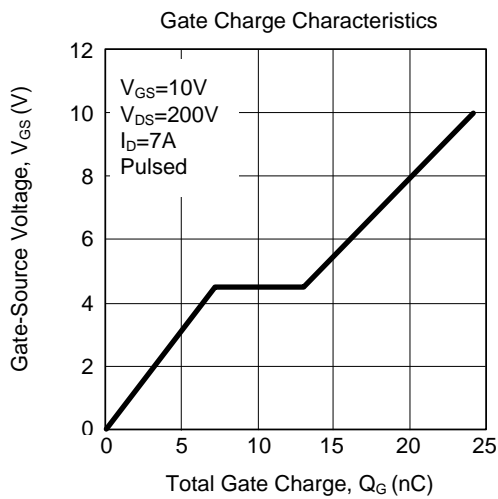
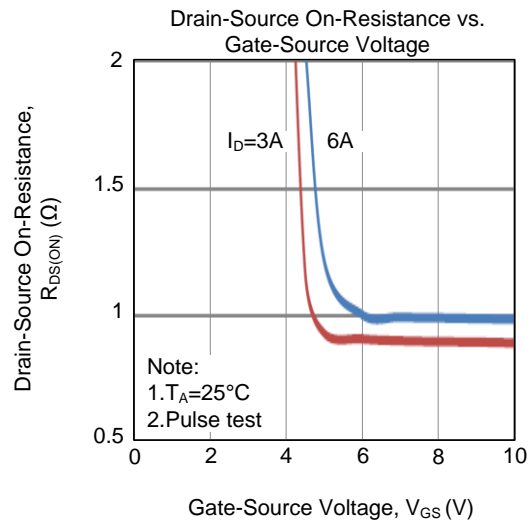
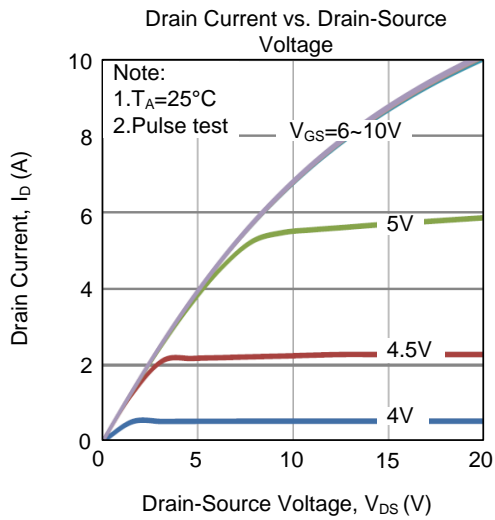


Unclamped Inductive Switching Test Circuit

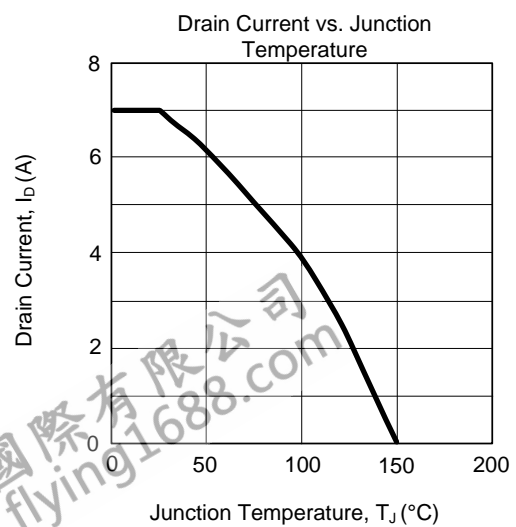
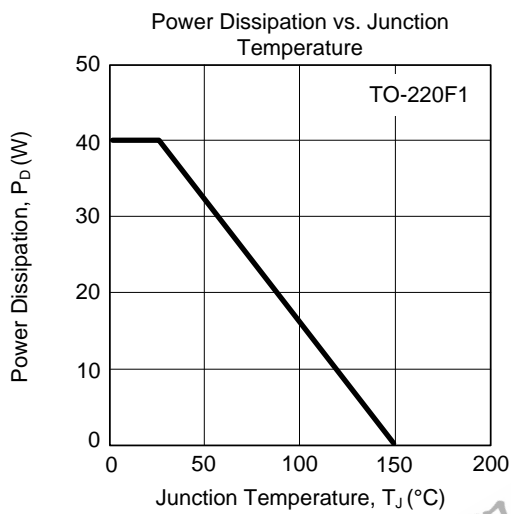
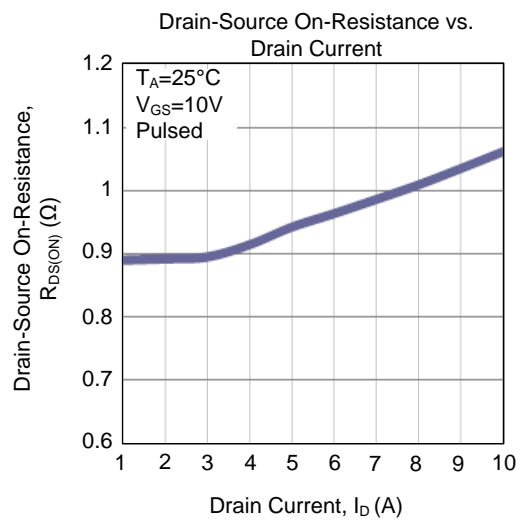
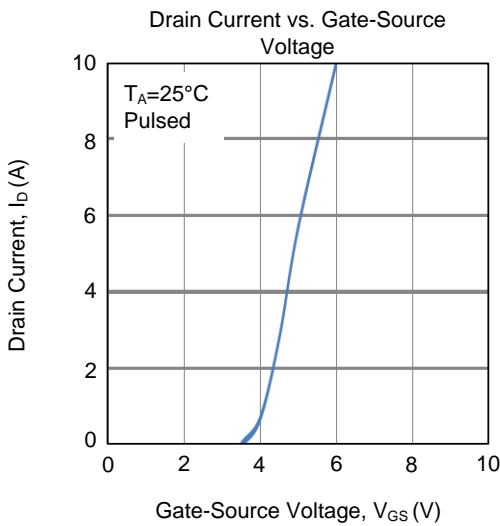
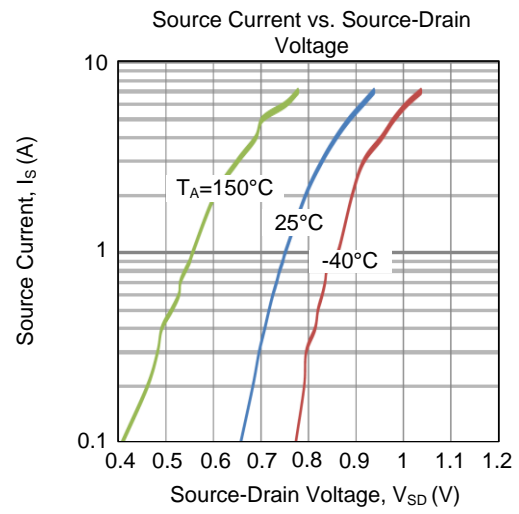
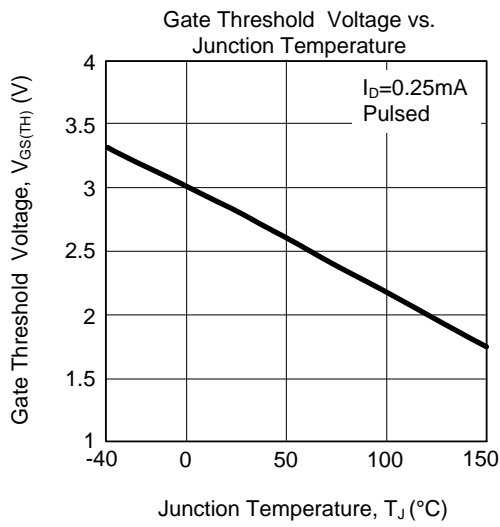


Unclamped Inductive Switching Waveforms

## ■ TYPICAL CHARACTERISTICS

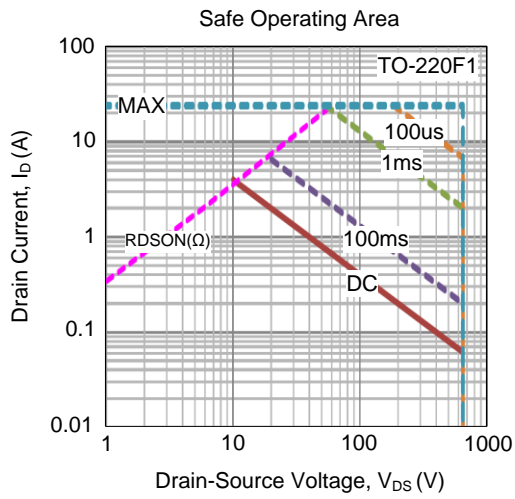


### TYPICAL CHARACTERISTICS (Cont.)





■ TYPICAL CHARACTERISTICS (Cont.)



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